

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLN. OF: ASPAR et al.

FILED: February 23, 2004

FOR: A METHOD OF PRODUCING A THIN LAYER OF ...

DOCKET: BREV 12370 CON4

MAIL STOP PATENT APPLICATION

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Dear Sir:

In connection with the above-entitled matter, Applicants hereby proffer U.S. Patent Office Forms PTO-1449 and PTO-892. The present application is a continuation under 37 CFR 1.53(b) of application Serial No. 09/777,516, wherein the references referred to in the enclosed U.S. Patent Office Forms PTO-1449 and PTO-892 have been previously submitted or cited. Accordingly, it is respectfully submitted that no copies of these references are believed necessary. The claims in the present application are believed to be patentably distinguished over these references.

This information disclosure statement is being made pursuant to the duty of disclosure imposed by law and formulated in 37 CFR 1.56(A). No representation is made that the information thus disclosed in fact constitutes prior art or that it is the closest prior art, inasmuch as 37 CFR 1.56(A) relies on a materiality concept which depends on subjectivity.

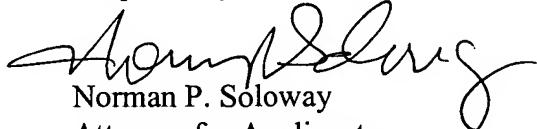
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In the event there are any fee deficiencies or additional fees are payable, please charge them (or credit any overpayment) to our Deposit Account No. 08-1391.

Respectfully submitted,



Norman P. Soloway  
Attorney for Applicants  
Reg. No. 24,315

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I hereby certify that this paper and the papers listed thereon are being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above, and is addressed to MAIL STOP PATENT APPLICATION, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Signature of person mailing:



Name of person mailing: Shauna Bronson

NPS:sb

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**INFORMATION DISCLOSURE CITATION**  
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**ASPAR ET AL**

**Filing Date**

Group A

**COPY**

## **U.S. PATENT DOCUMENTS**

## FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** (*Including Author, Title, Date, Pertinent Pages, Etc.*)


EXAMINER

D.B. CONN

**DATE CONSIDERED**

12-21-04

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dar	4,704,302	11/3/87	Bruel et al			
	5,234,535	8/10/93	NBeyer et al			
	5,494,835	2/27/96	Bruel			
	5,804,086	9/8/98	Bruel			
	5,817,368	10/6/98	Hashimoto			
	5,863,830	1/26/99	Bruel et al			
	5,897,331	4/27/99	Sopori			
	5,633,174	5/27/97	Li			
↓	5,250,446	10/5/93	Osowa et al			

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						YES	NO
Dar	WO95/20824	8/3/95	PCT			✓	
↓	EP 0703 609	3/27/96	EPO			✓	
	0 660 140	6/28/95	EPO			✓	
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Dar	Evans, J.H., "An interbubble fracture mechanism of blister formation on Helium-Irradiated Metals," Journal of Nuclear Materials, Vol 68, 1997, pp 129-140

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Dar. Cowd	12-21-07

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DM, CONCNS	12-21-01

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D. M. Corvis

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FORM PTO-1449	SERIAL NO.	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE	GROUP ART UNIT
	APPLICANT(S):	Aspar et al.

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

U.S. PATENTS

<u>PATENT NO.</u>	<u>INVENTOR</u>	<u>ISSUE DATE</u>
4,179,324	12/18/79	Kirkpatrick
5,110,748	5/5/92	Sarma
5,310,446	5/10/94	Konishi et al.
5,661,333	8/26/97	Bruel et al.

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<u>DOCUMENT NO.</u>	<u>COUNTRY</u>	<u>DATE</u>
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Haisma et al., Silicon-on-Insulator Wafer Bonding-Wafer Thinning-Technological Evaluations, Japanese Journal of Applied Physics, 28(1989), Aug., No. 8, Part 1, Tokyo, Japan, pp. 1426-1443

*D. A. Colby**12-21-01*

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		APPLICANT(S): Aspar et al.	

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
Dm	A1 4,179,324	12/18/79	Kirkpatrick	156/230	11/28/77
	A2 5,110,748	5/5/92	Sarma	437/51	7/22/91
	A3 5,310,446	5/10/94	Konishi et al.	117/58	7/13/92
↓	A4 5,661,333	8/26/97	Bruel et al.	257/618	1/25/95
A5					
A6					
A7					
A8					

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Dm	A9 2725074	3/29/96	France			X
↓	A10 0355913	2/28/90	EPO		X	
↓	A11 0504714	9/23/92	EPO		X	

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Dm	A12	Silicon-On-Insulator, <i>European Semiconductor</i> , March, 1997, pages 17 and 18
	A13	Aspar et al., SMART-CUT®: The basic fabrication process for UNIBOND® SOI wafers, <i>SEM</i> 1996, pp. 37-46
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D.M. (ALTERS)

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ASPAR ET AL

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*EXAMINER INITIAL	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
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<i>Dave</i>		Helium Bubble and Blister Formation for Nickel and An AMorphous Fe-Ni-Mo-B Alloy During 5 keV He+-Irradiation at Temperatures Between 200 K and 600 K, Swijgenhoven, Stals and Knuyt, Nuclear Instruments and Methods 209/210 (1983) pgs. 461-468
<i>Dave</i>		Infrared Spectroscopy of chemically bonded hydrogen at voids and defects in silicon, Stein, Myers and Follstaedt, J. Appl. Phys. 73(b6), 15 March 1993, pgs. 2755-2764

EXAMINER D.M. COLLINS DATE CONSIDERED 12-21-01

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**U.S. PATENT DOCUMENTS**

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Dme | Ion Implantation In Semiconductors 1976, Chernow, Borders and Brice, Plenum Press, New York and London, Radiation  
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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE  
(Modified) PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)

(37 CFR 1.98(b))

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BREV 12370 CON 2

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## **U.S. PATENT DOCUMENTS**

**FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION**

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							YES	NO
DAC		7 0 3 6 0 9 A1	3/27/96	EPO	H01L	21/762		X
		5 3 3 5 5 1 A1	9/15/92	EPO	H01L	21/265		X
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↓		2 6 8 1 4 7 2	9/18/91	France	H01L	21/265		X

**OTHER DOCUMENTS** (Including Author, Title, Date\*\*, Relevant Pages, Place of Publication\*\*\*)

DMC		<p>"Silicon on insulator Material Technology" Bruel, M.  <i>Electronic Letters</i>; 31 (1995) 06 July; No. 14; pgs 1201-1202</p>
DMC		<p>"Investigation of the Bubble Formation Mechanism in a-Si:H films by Fourier-transform infrared microspectroscopy" Mishima et al  <i>Japan Allied Physics</i>; 64(8); October 15, 1988; pgs. 3972-3974</p>

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